

Silicon PNP Power Transistors

2SA1263N

DESCRIPTION

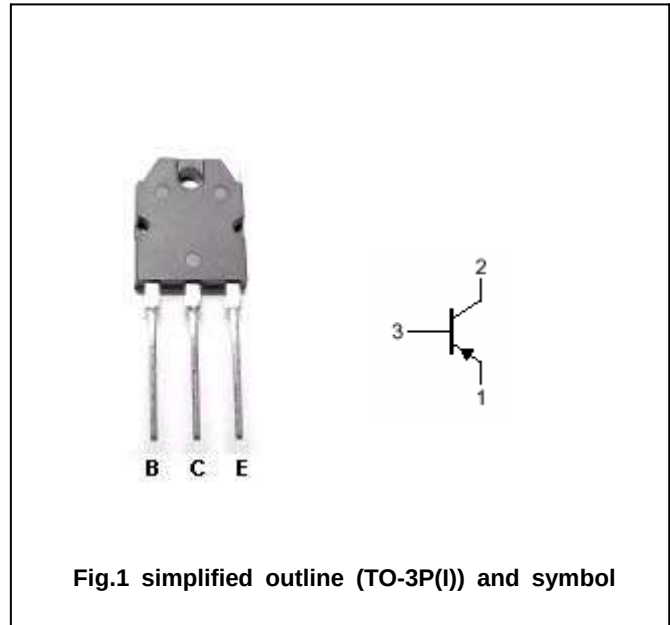
- With TO-3P(I) package
- Complement to type 2SC3180N
- 2SA1263 with short pin

APPLICATIONS

- Power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-6	A
I_B	Base current		-0.6	A
P_T	Total power dissipation	$T_C=25^{\circ}\text{C}$	60	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA, I_B=0$	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A; I_B=-0.5A$		-1.0	-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-3A; V_{CE}=-5V$		-0.95	-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V; I_E=0$			-5	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-5	μA
h_{FE-1}	DC current gain	$I_C=-1A; V_{CE}=-5V$	55		160	
h_{FE-2}	DC current gain	$I_C=-3A; V_{CE}=-5V$	35			
f_T	Transition frequency	$I_C=-1A; V_{CE}=-5V$		30		MHz
C_{ob}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		290		pF

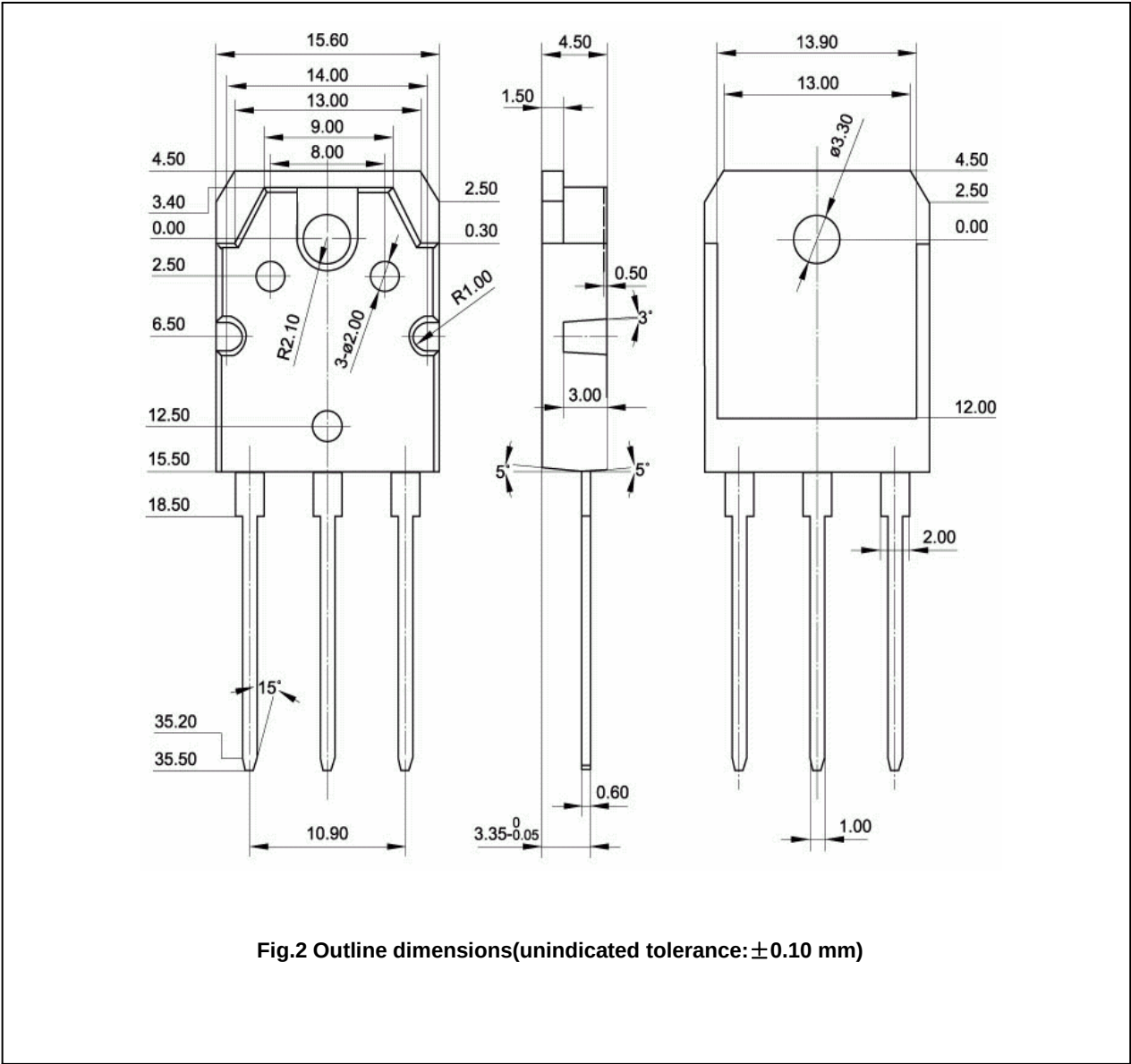
◆ h_{FE-1} Classifications

R	O
55-110	80-160

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PACKAGE OUTLINE



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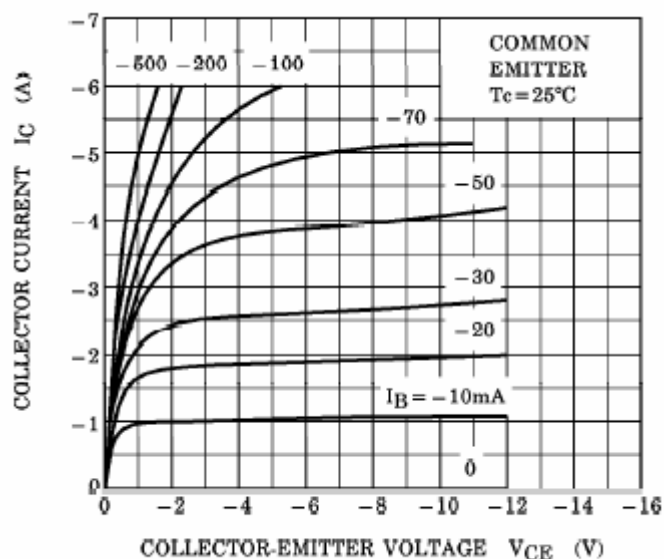


Fig.3 Static Characteristic

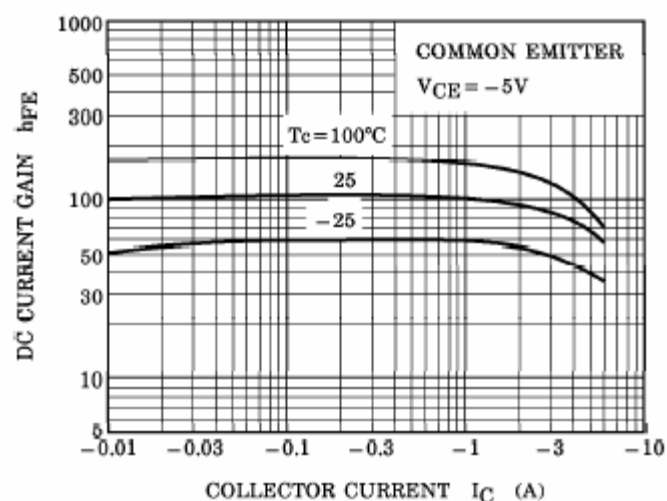


Fig.5 DC current Gain

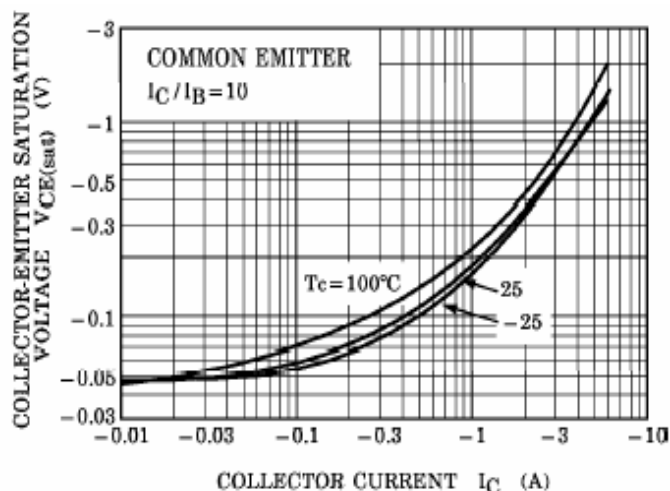


Fig.4 Collector-Emitter Saturation Voltage

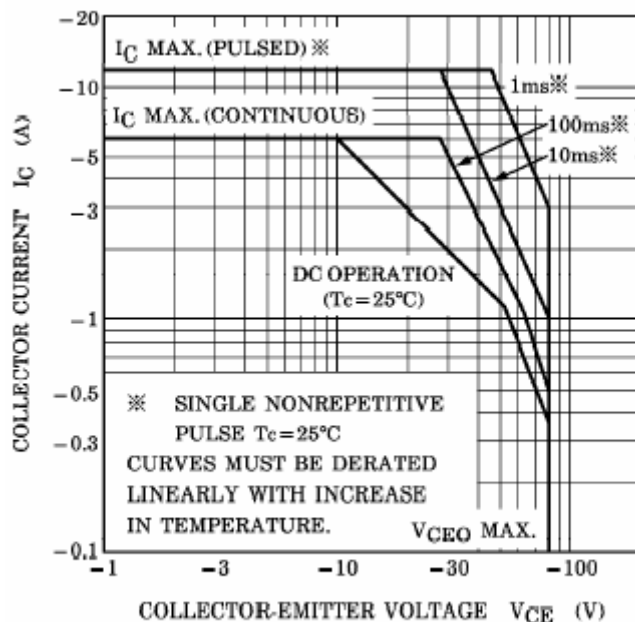


Fig.6 Safe Operating Area